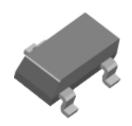
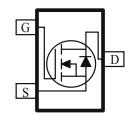
### N-Channel 20V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY			
$V_{DS}(V)$	$V_{DS}(V)$ $\eta_{DS(on)}(\Omega)$ $I_{D}(A)$		
20	$0.058 @V_{CS} = 4.5 V$	2.0	
	$0.082 @V_{CS} = 2.5V$	1.7	

- Low  $r_{DS(on)}$  provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SC70-3 saves board space
- Fast switching speed
- High performance trench technology





ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	Maximum	Units	
Drain-Source Voltage			20	V	
Gate-Source Voltage			±8	V	
Continuous Drain Current <sup>a</sup>	$T_A=25^{\circ}C$	T	2.0		
Continuous Drain Current	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	ц	1.7	A	
Pulsed Drain Current <sup>b</sup>		$I_{DM}$	±20		
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	1.6	A	
D D: : ,: a	$T_A=25^{\circ}C$	D	0.34	w	
Power Dissipation <sup>a</sup>	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	LD	0.22	VV	
Operating Junction and Storage Temperature Range		$T_{J}, T_{stg}$	-55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Maximum	Units	
Maximum Junction-to-Ambient <sup>a</sup>	t <= 5 sec	D	100	00/11/	
	Steady-State	$R_{THJA}$	166	°C/W	

#### Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

SPECIFICATIONS (T <sub>A</sub> = 25°C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Symbol Test Conditions		Limits			
r ar ameter	Symbol			Тур	Max	Unit	
Static							
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \text{ uA}$	0.7			V	
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			±100	nA	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
_	1088	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10		
On-State Drain Current <sup>A</sup>	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	10			Α	
Drain-Source On-Resistance <sup>A</sup>		$V_{GS} = 4.5 \text{ V}, I_D = 2.0 \text{ A}$			58	mΩ	
Drain-Source On-Resistance	$r_{DS(on)}$	$V_{GS} = 2.5 \text{ V}, I_D = 1.7 \text{ A}$			82	11152	
Forward Tranconductance <sup>A</sup>	$g_{ m fs}$	$V_{DS} = 10 \text{ V}, I_D = 2.0 \text{ A}$		11.3		S	
Diode Forward Voltage	$V_{\mathrm{SD}}$	$I_S = 1.6 \text{ A}, V_{GS} = 0 \text{ V}$		0.75		V	
Dynamic <sup>b</sup>							
Total Gate Charge	$Q_{g}$			7.5			
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 2.0 \text{ A}$		0.6		nC	
Gate-Drain Charge	$Q_{gd}$			1.0			
Input Capacitance	$C_{iss}$	V -15 V V -0 V		720			
Output Capacitance	$C_{oss}$	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V},$		165		pF	
Reverse Transfer Capacitance	$C_{rss}$	f = 1MHz		60		1	
Turn-On Delay Time	$t_{d(on)}$			8			
Rise Time	$t_{\rm r}$	$V_{DD} = 10 \text{ V},  R_L = 15 \Omega,  I_D = 1 \text{ A},$		24			
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 4.5 \text{ V}$		35		ns	
Fall-Time	$t_{ m f}$			10		1	

#### Notes

- a. Pulse test:  $PW \le 300us duty cycle \le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

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# Typical Electrical Characteristics (N-Channel)

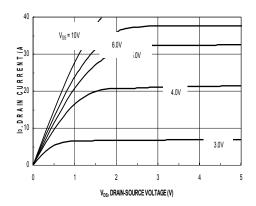


Figure 1. On-Region Characteristics

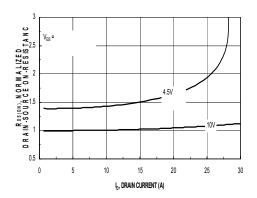


Figure 3. On Resistance Vs Vgs Voltage

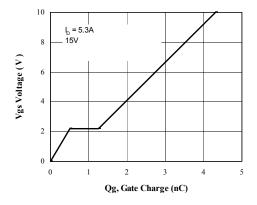


Figure 5. Gate Charge Characteristics

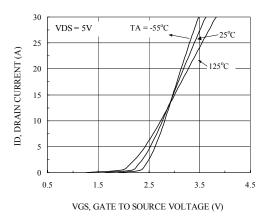


Figure 2. Body Diode Forward Voltage Variation with Source Current and Temperature

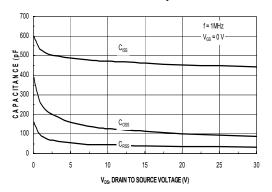


Figure 4. Capacitance Characteristics

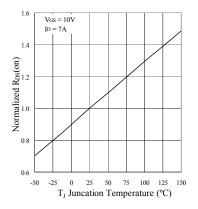


Figure 6. On-Resistance Variation with Temperature

## Typical Electrical Characteristics (N-Channel)

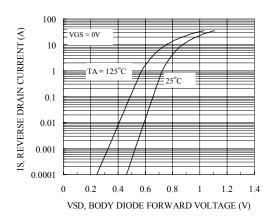


Figure 7. Transfer Characteristics

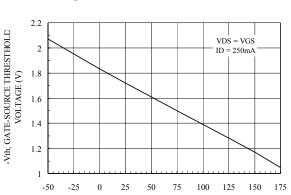


Figure 9. Vth Gate to Source Voltage Vs Temperature

0.1

0.01

0.001

0.0001

0.001

0.01

TA, AMBIENT TEMPERATURE (°C)

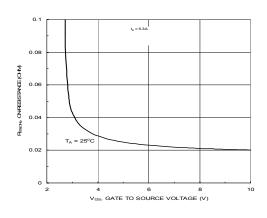


Figure 8. On-Resistance with Gate to Source Voltage

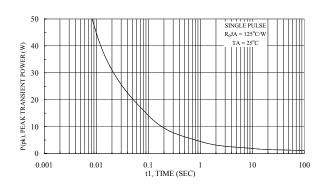
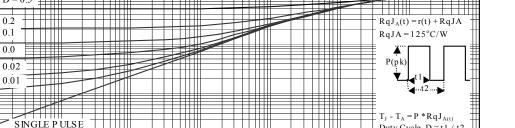


Figure 10. Single Pulse Maximum Power Dissipation

Duty Cycle, D = t1

100

1000



**Normalized Thermal Transient Junction to Ambient** 

Figure 11. Transient Thermal Response Curve

t1, TIME (sec)